

HAT1038R, HAT1038RJ

Silicon P Channel Power MOS FET
High Speed Power Switching

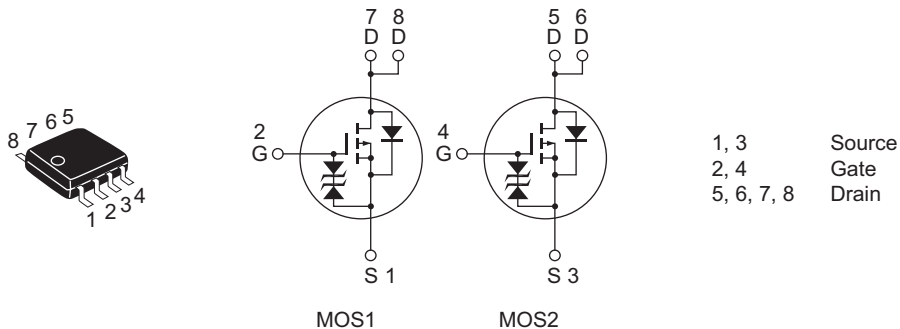
REJ03G1150-0500
(Previous: ADE-208-663C)
Rev.5.00
Sep 07, 2005

Features

- For Automotive Application (at Type Code "J")
- Low on-resistance
- Capable of 4 V gate drive
- High density mounting

Outline

RENESAS Package code: PRSP0008DD-D
(Package name: SOP-8 <FP-8DAV>)



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	-60	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	-3.5	A
Drain peak current	I _{D (pulse)} ^{Note 1}	-28	A
Body-drain diode reverse drain current	I _{DR}	-3.5	A
Avalanche current	HAT1038R	—	—
	HAT1038RJ	-3.5	A
Avalanche energy	HAT1038R	—	—
	HAT1038RJ	1.05	mJ
Channel dissipation	P _{ch} ^{Note 2}	2	W
Channel dissipation	P _{ch} ^{Note 3}	3	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. 1 Drive operation: When using the glass epoxy board (FR4 40 × 40 × 1.6 mm), PW ≤ 10 s

3. 2 Drive operation: When using the glass epoxy board (FR4 40 × 40 × 1.6 mm), PW ≤ 10 s

4. Value at T_{ch} = 25°C, R_g ≥ 50 Ω

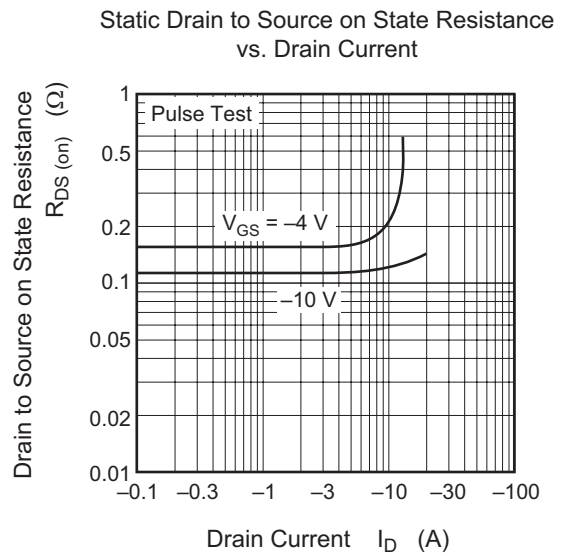
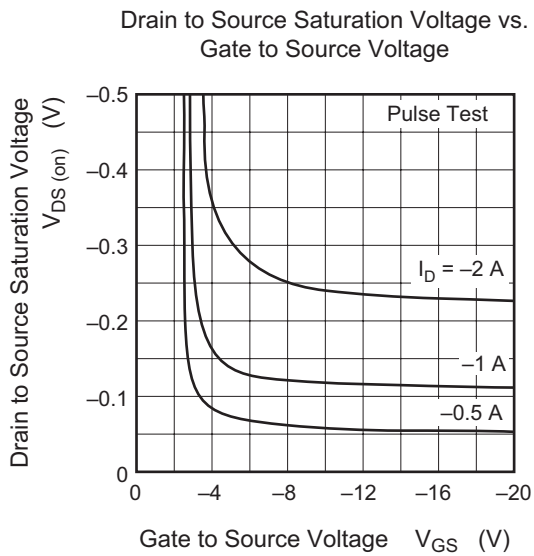
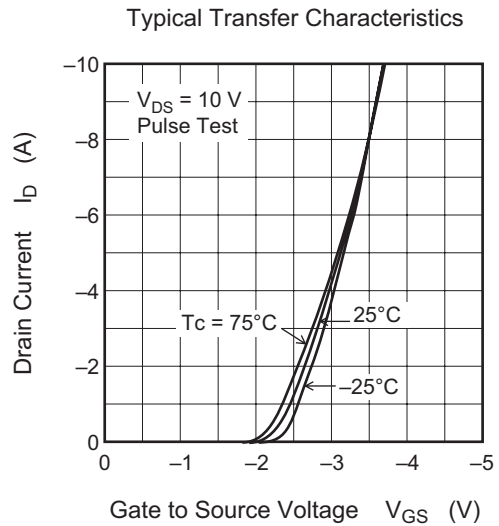
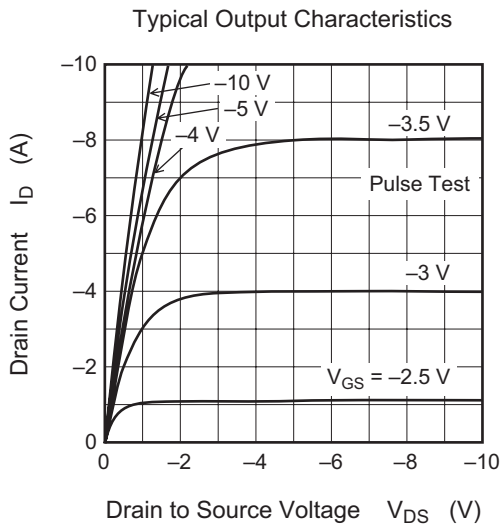
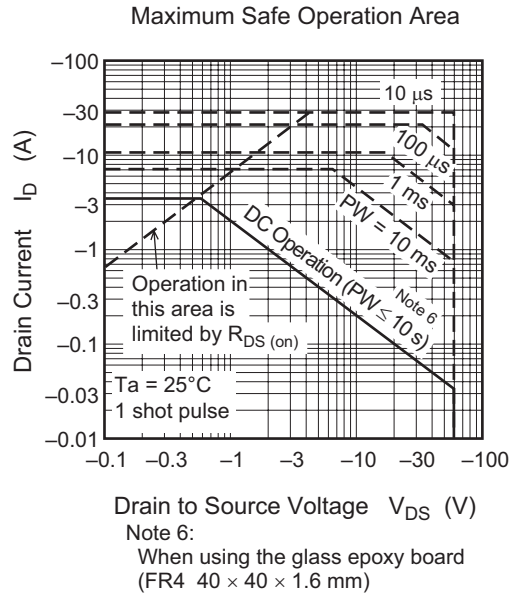
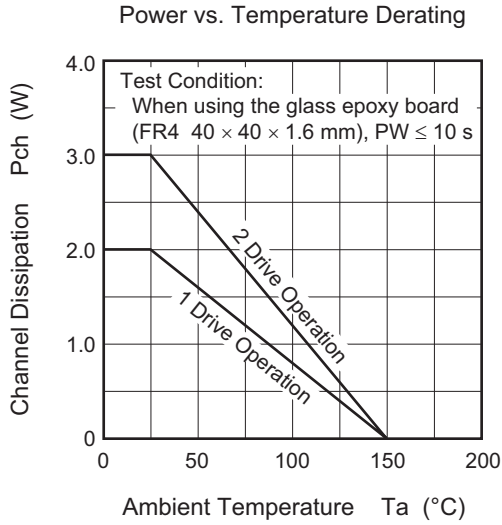
Electrical Characteristics

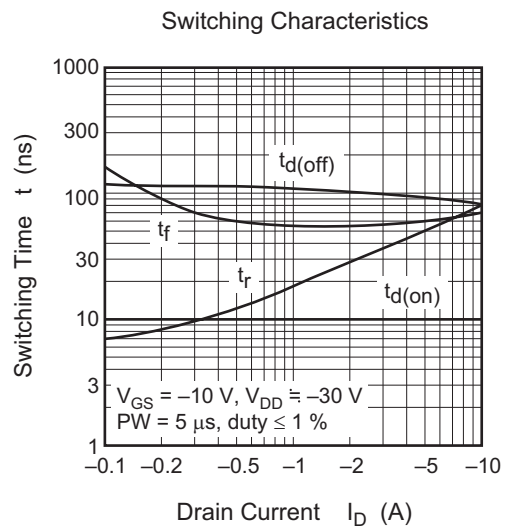
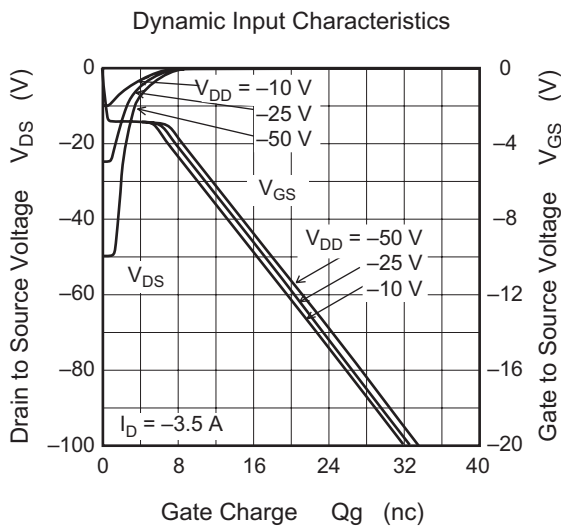
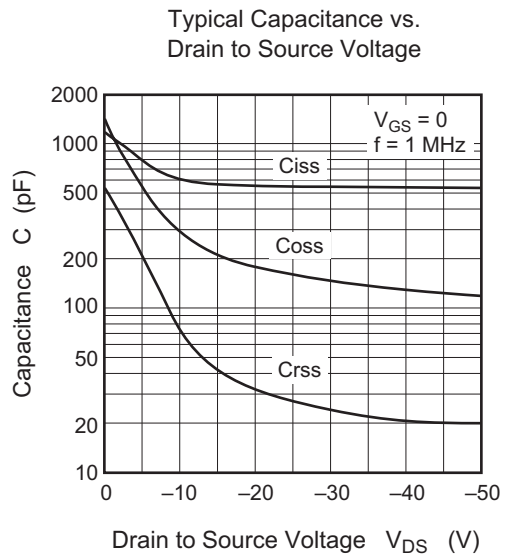
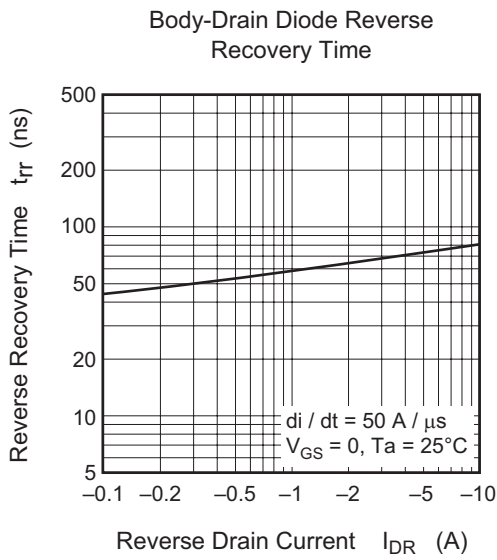
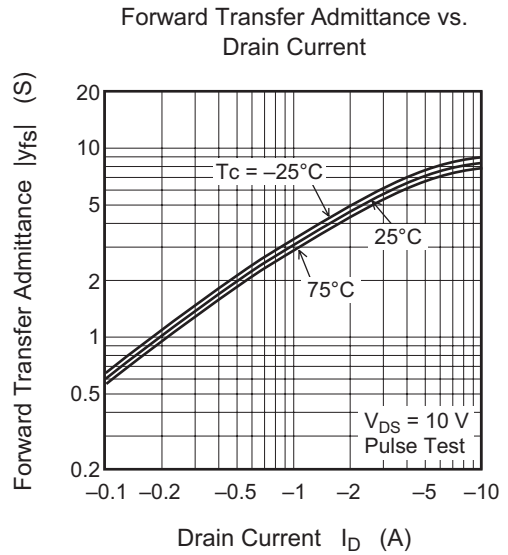
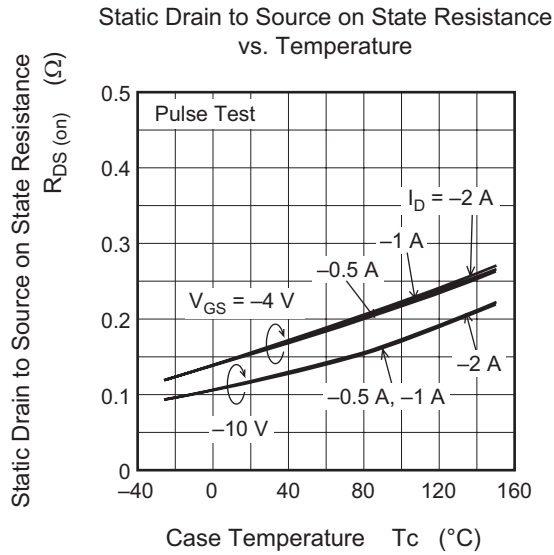
(Ta = 25°C)

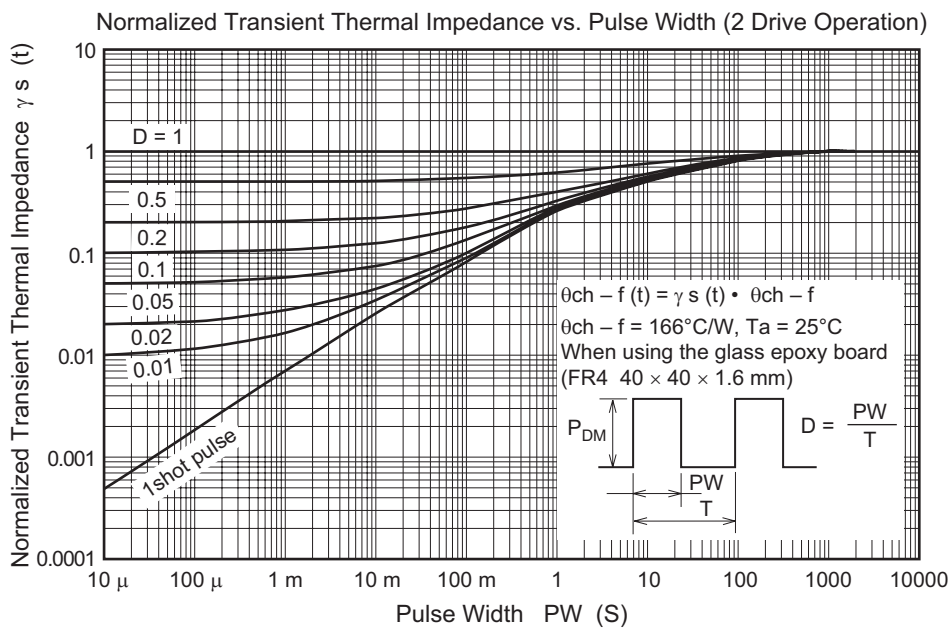
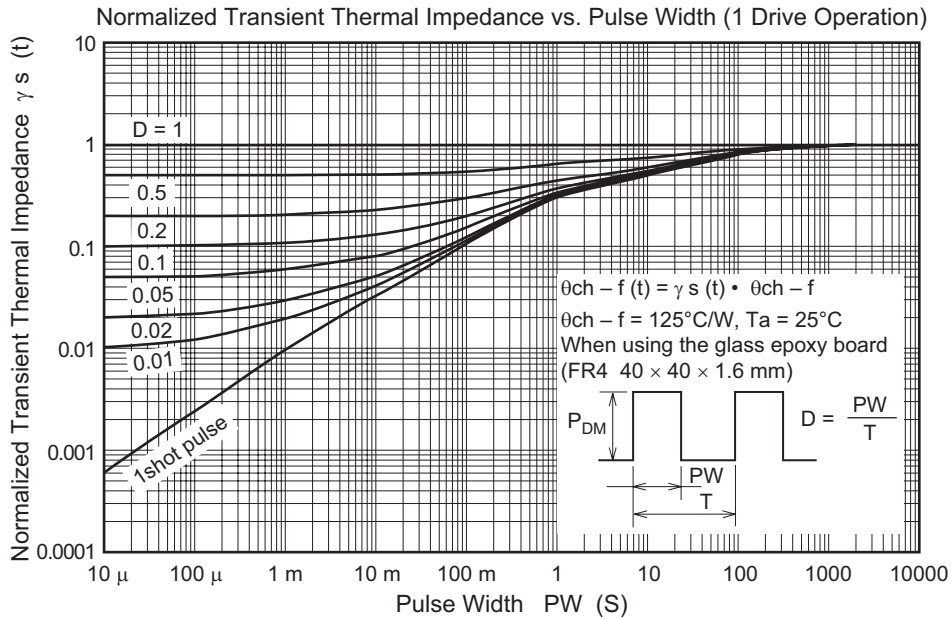
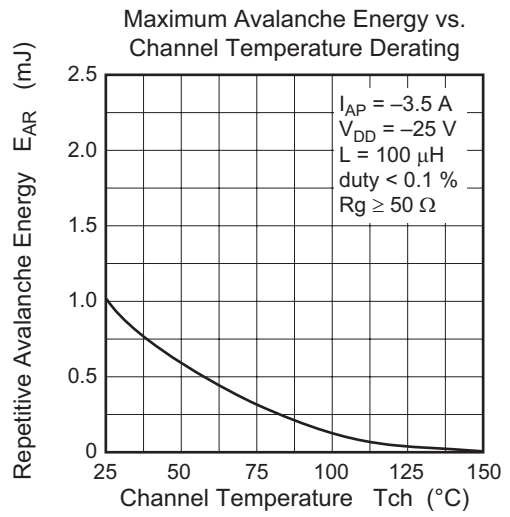
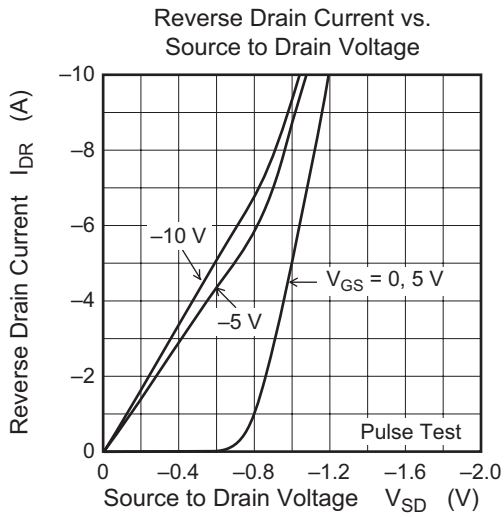
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR) DSS}	-60	—	—	V	I _D = -10 mA, V _{GS} = 0
Gate to source leak voltage	V _{(BR) GSS}	±20	—	—	V	I _G = ±100 μA, V _{DS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	μA	V _{GS} = ±16 V, V _{DS} = 0
Zero gate voltage drain current	HAT1038R	I _{DSS}	—	-1	μA	V _{DS} = -60 V, V _{GS} = 0
	HAT1038RJ	I _{DSS}	—	-0.1	μA	
Zero gate voltage drain current	HAT1038R	I _{DSS}	—	—	μA	V _{DS} = -48 V, V _{GS} = 0 Ta = 125°C
	HAT1038RJ	I _{DSS}	—	-10	μA	
Gate to source cutoff voltage	V _{GS (off)}	-1.2	—	-2.2	V	V _{DS} = -10 V, I _D = -1 mA
Static drain to source on state resistance	R _{DS (on)}	—	0.12	0.15	Ω	I _D = -2 A, V _{GS} = -10 V ^{Note 5}
	R _{DS (on)}	—	0.16	0.23	Ω	
Forward transfer admittance	y _{fs}	3	4.5	—	S	I _D = -2 A, V _{DS} = -10 V ^{Note 5}
Input capacitance	C _{iss}	—	600	—	pF	V _{DS} = -10 V V _{GS} = 0 f = 1 MHz
Output capacitance	C _{oss}	—	290	—	pF	
Reverse transfer capacitance	C _{rss}	—	75	—	pF	
Turn-on delay time	t _{d (on)}	—	11	—	ns	V _{GS} = -10 V, I _D = -2 A, V _{DD} ≅ -30 V
Rise time	t _r	—	30	—	ns	
Turn-off delay time	t _{d (off)}	—	100	—	ns	
Fall time	t _f	—	55	—	ns	
Body-drain diode forward voltage	V _{DF}	—	-0.98	-1.28	V	I _F = -3.5 A, V _{GS} = 0 ^{Note 5}
Body-drain diode reverse recovery time	t _{rr}	—	70	—	ns	I _F = -3.5 A, V _{GS} = 0 di _F /dt = 50 A/μs

Note: 5. Pulse test

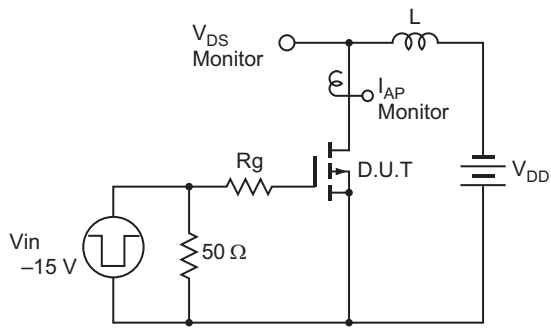
Main Characteristics



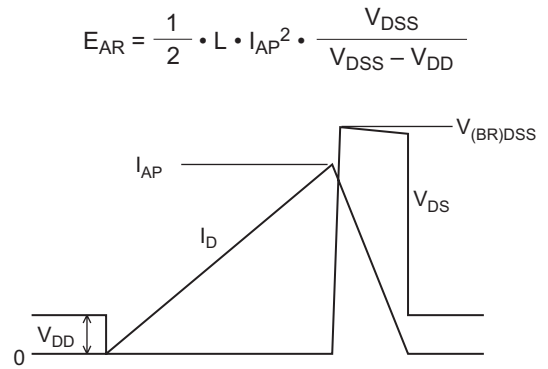




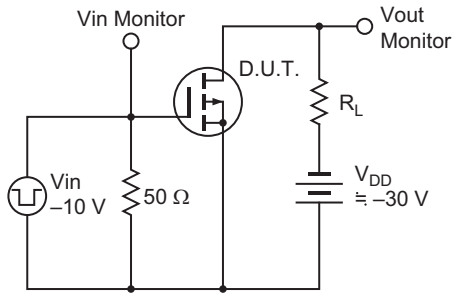
Avalanche Test Circuit



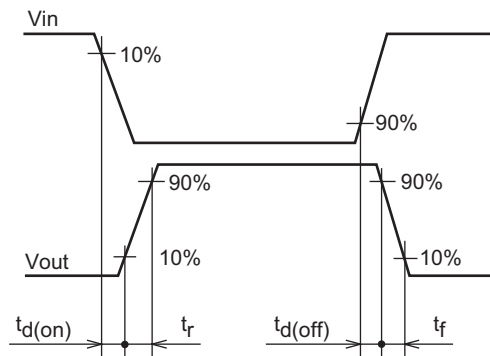
Avalanche Waveform



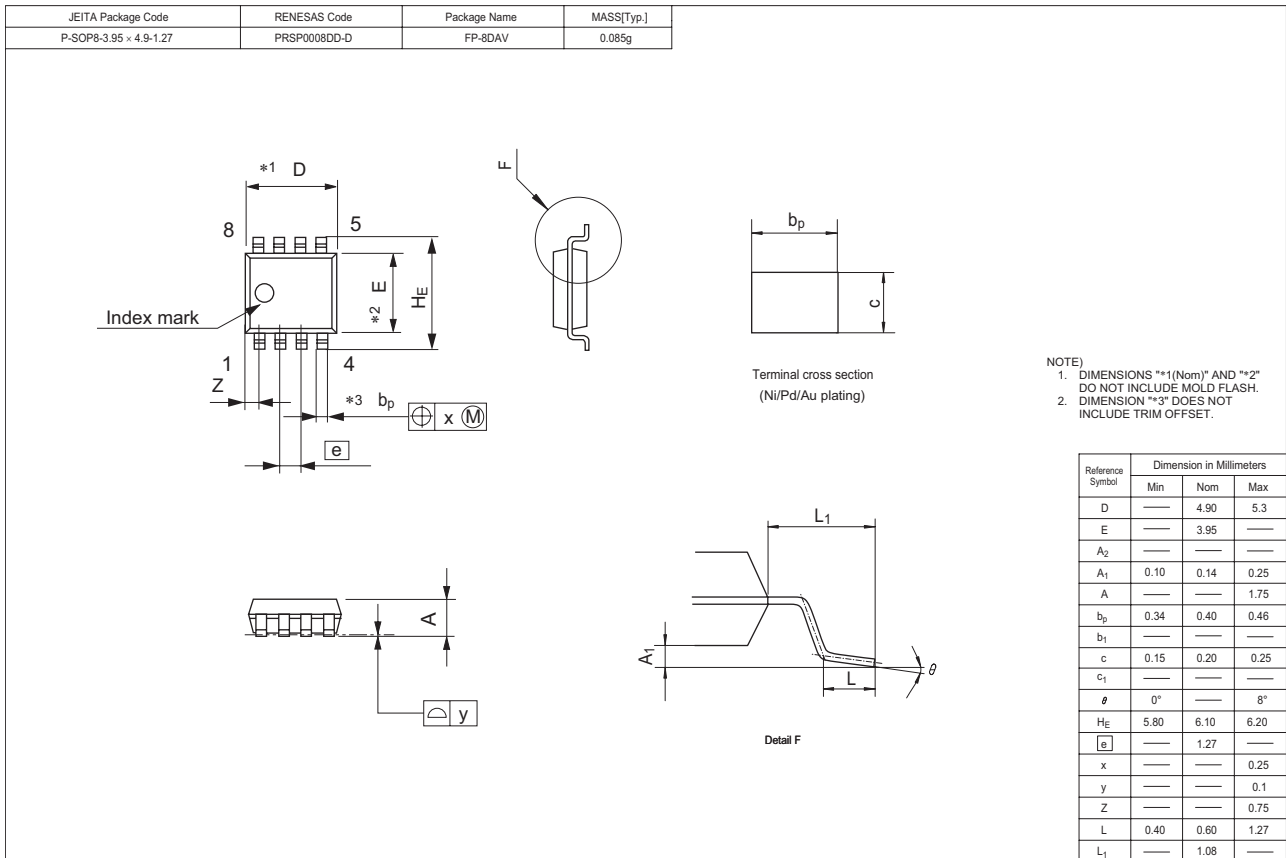
Switching Time Test Circuit



Switching Time Waveform



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT1038R-EL-E	2500 pcs	Taping
HAT1038RJ-EL-E	2500 pcs	Taping

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